

# Matthew P West

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8431419/publications.pdf>

Version: 2024-02-01

9  
papers

115  
citations

1307594

7  
h-index

1588992

8  
g-index

9  
all docs

9  
docs citations

9  
times ranked

137  
citing authors

#	ARTICLE	IF	CITATIONS
1	Substrate dependent resistive switching in amorphous-HfO <sub>x</sub> memristors: an experimental and computational investigation. <i>Journal of Materials Chemistry C</i> , 2020, 8, 5092-5101.	5.5	25
2	Synthetic Engineering of Morphology and Electronic Band Gap in Lateral Heterostructures of Monolayer Transition Metal Dichalcogenides. <i>ACS Nano</i> , 2020, 14, 6323-6330.	14.6	24
3	Towards a better understanding of the forming and resistive switching behavior of Ti-doped HfO <sub>x</sub> RRAM. <i>Journal of Materials Chemistry C</i> , 2022, 10, 5896-5904.	5.5	16
4	Impact of the thermal environment on the analog temporal response of HfO <sub>x</sub> -based neuromorphic devices. <i>Applied Physics Letters</i> , 2020, 116, .	3.3	13
5	Experimental and computational analysis of thermal environment in the operation of HfO <sub>2</sub> memristors. <i>AIP Advances</i> , 2020, 10, .	1.3	13
6	Impact of titanium doping and pulsing conditions on the analog temporal response of hafnium oxide based memristor synapses. <i>Journal of Applied Physics</i> , 2022, 131, .	2.5	11
7	Impact of oxygen concentration at the HfO <sub>x</sub> /Ti interface on the behavior of HfO <sub>x</sub> filamentary memristors. <i>Journal of Materials Science</i> , 2022, 57, 9299-9311.	3.7	8
8	Impact of Synthesized MoS <sub>2</sub> Wafer-Scale Quality on Fermi Level Pinning in Vertical Schottky-Barrier Heterostructures. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 39860-39871.	8.0	5
9	Preferential growth of crystalline MoS <sub>2</sub> on patterned Ni channels in contact with Au thin films. , 2021, , .		0